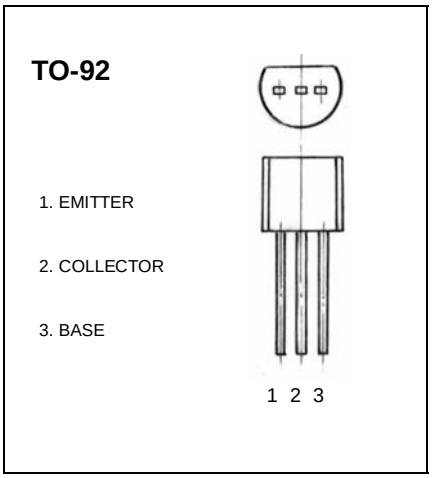
Transys Electronics LIMITED

TO-92 Plastic-Encapsulated Transistors

2SA673 TRANSISTOR (PNP)



FEATURE

Power dissipation

P_{CM} : 0.4 W (Tamb=25℃)

Collector current

$I_{CM:}$ -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -10μA , I_E=0	-35			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=-1 mA , I_B=0	-35			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=-10μA, I_C=0	-4			V
Collector cut-off current	I_{CBO}	V_{CB}= -20 V , I_E=0			-0.5	μA
DC current gain	$h_{FE(1)}$*	V_{CE}=-3V, I_C= -10mA	60		320	
	$h_{FE(2)}$	V_{CE}=-3 V, I_C=-500mA	10			
Collector-emitter saturation voltage	V_{CEsat} *	I_C= -150mA, I_B=-15mA			-0.6	V
Base-emitter voltage	V_{BE}	V_{CE}=-3 V, I_C=-10mA			-0.75	V

*Measured using pulse

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range	60-120	100-200	160-320